

MMD60R900P

600V 0.9Ω N-channel MOSFET

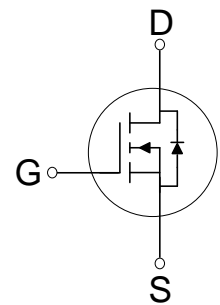
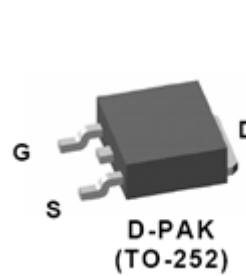
■ Description

MMD60R900P is power MOSFET using magnachip's advanced super junction technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of Low EMI to designers as well as low switching loss.

■ Key Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.9	Ω
$V_{TH,typ}$	3	V
I_D	4.5	A
$Q_{g,typ}$	12.3	nC

■ Package & Internal Circuit



■ Features

- Low Power Loss by High Speed Switching and Low On-Resistance
- 100% Avalanche Tested
- Green Package – Pb Free Plating, Halogen Free

■ Applications

- PFC Power Supply Stages
- Switching Applications
- Adapter
- Motor Control
- DC – DC Converters

■ Ordering Information

Order Code	Marking	Temp. Range	Package	Packing	RoHS Status
MMD60R900PRH	60R900P	-55 ~ 150°C	TO-252 (DPAK)	Reel & Tube	Halogen Free